

Novel Diamond Semiconductors Operate at Highest Power Ever

Prof. Makoto Kasu, Saga University

Niloy Chandra Saha, Toshiyuki Oishi (SU)

Seong-Woo Kim (Adamant Namiki Precision Jewel)

- 1) Diamond semiconductor possessing ultimate power capability
- 2) Wide and high-pure diamond wafer growth technology
- 3) Realization of diamond semiconductor devices with a novel principle
- 4) Output power density of 179 MW/cm^2 , which is the highest ever reported
- 5) Resulting output power density boosts the output power of Beyond-5G base stations and power control in electric car vehicles
- 6) Long-range reliability enables the of diamond semiconductor devices in space

Fig. 1. Demand for high-frequency high-power semiconductors for Beyond 5G communications

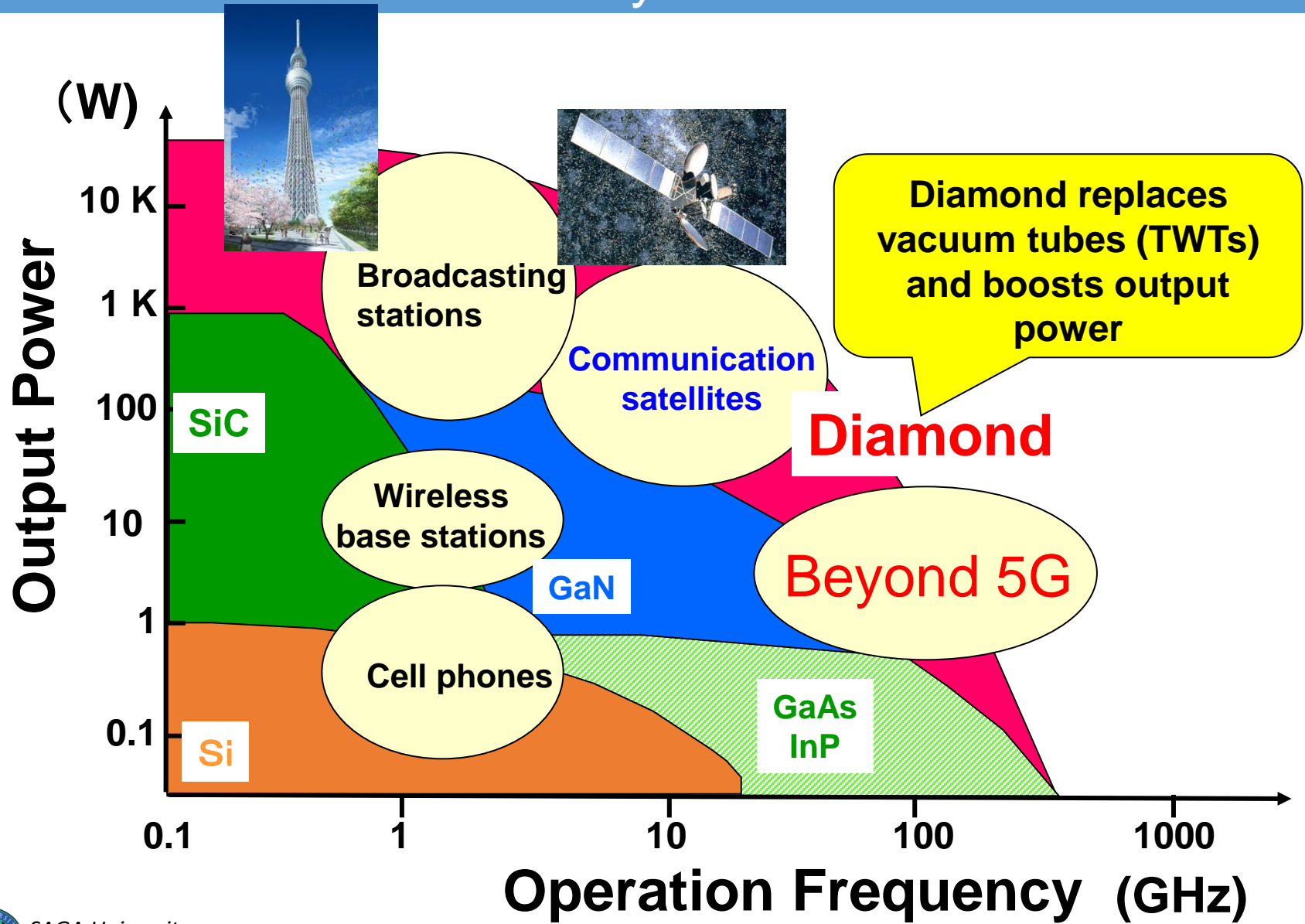
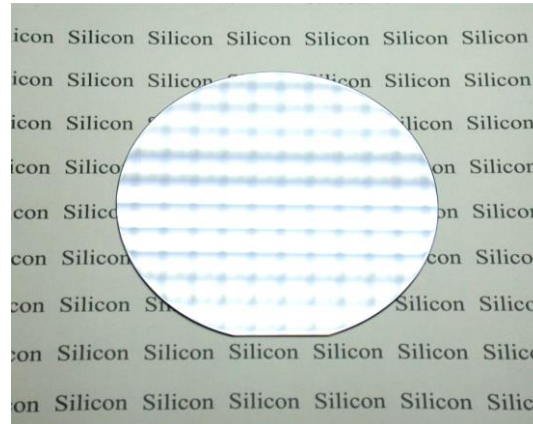


Fig. 2. Diamond's superior physical properties and expected device capabilities

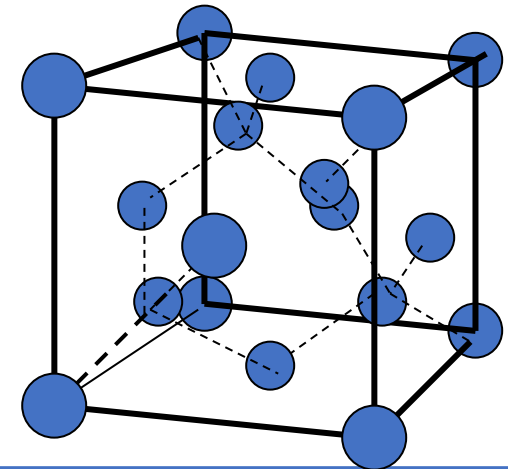
Diamond



Silicon



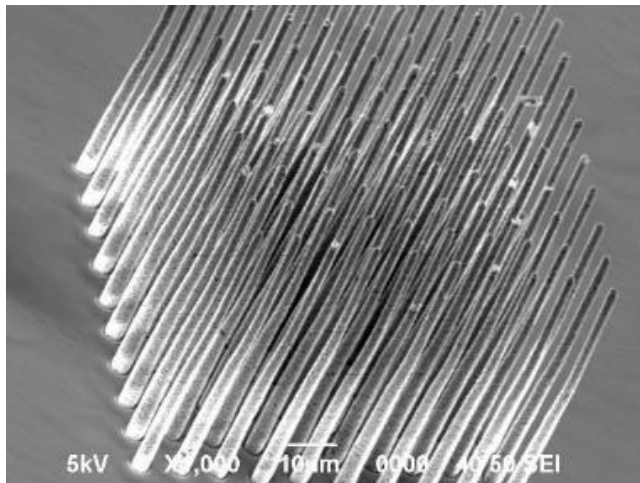
Crystal structure



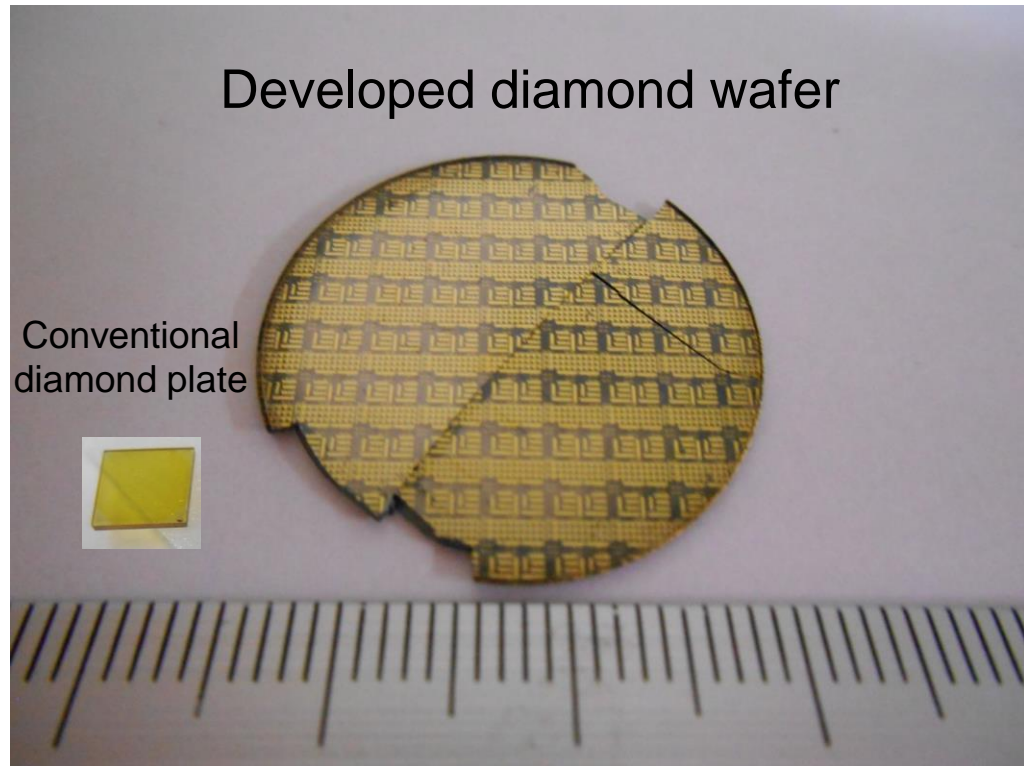
	Silicon	SiC	GaN	Diamond	Diamond's properties
Bandgap energy	1	2.9	3.0	4.9	5 times high temperature
Breakdown field	1	9.3	16.6	33	33 times high voltage
Thermal conductivity	1	3.8	1.2	17	17 times heat dissipation, less temperature rise
Baliga's FOM	1	580	3800	49 000	50 000 times high power and high efficient device characteristics
Johnson's FOM	1	420	1100	1225	1200 times high-speed power device characteristics for Beyond 5G

Fig. 3. Technology (1) Wide and high-pure diamond wafer growth technology

Microneedle method and sapphire substrate enable the growth of wide-scaled high-pure diamond wafer



Microneedle method

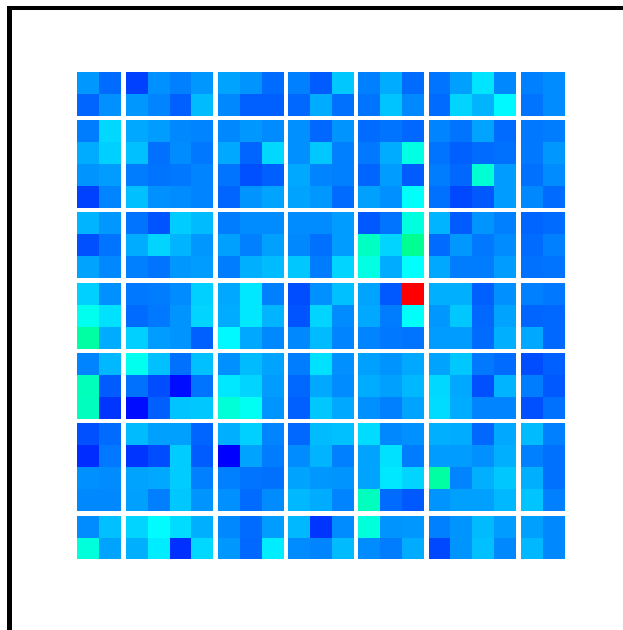


- Mass-production technology of world's widest 1 inch
- Sapphire substrate makes high pure and max. 6 inch possible

Highest quality diamond confirmed by Synchrotron



Saga Synchrotron Light Center



High crystal quality on entire surface

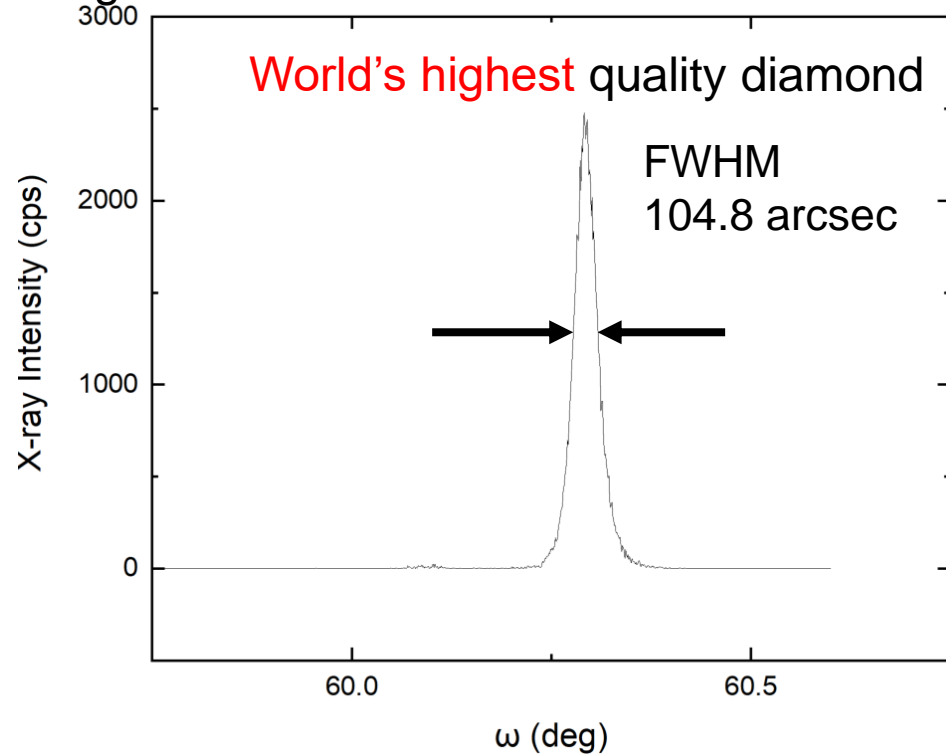
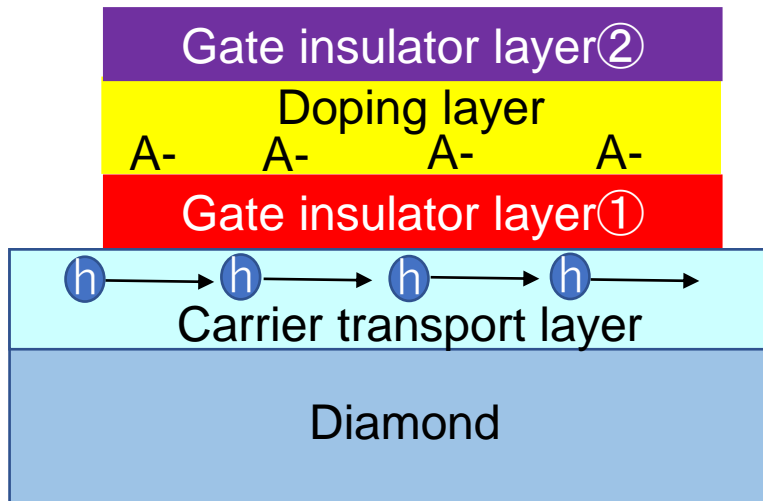


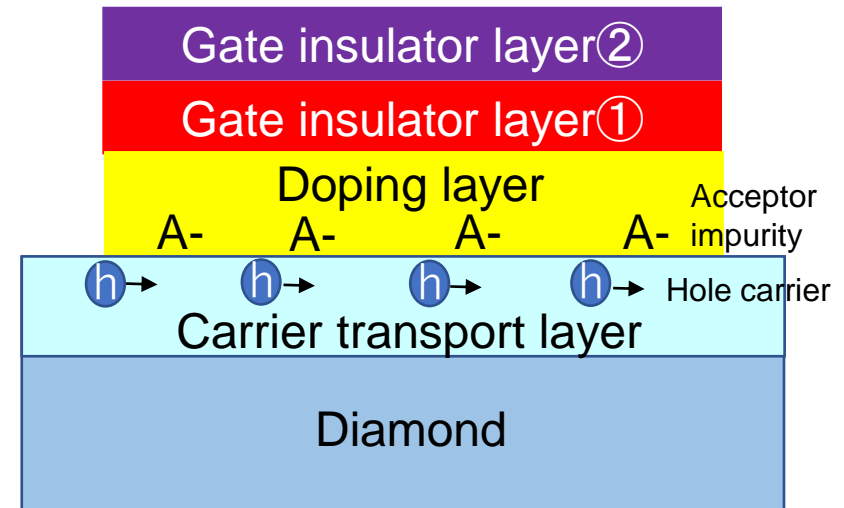
Fig. 4. Technology (2) Diamond semiconductor devices with novel principle

Novel structure



- Doping layer and carrier transport layer are spastically separated
- Carriers (h) are not influenced by acceptor impurities (A⁻), and mobility increases
- Spastically separated doping layer and carrier transport layer leads to no degradation

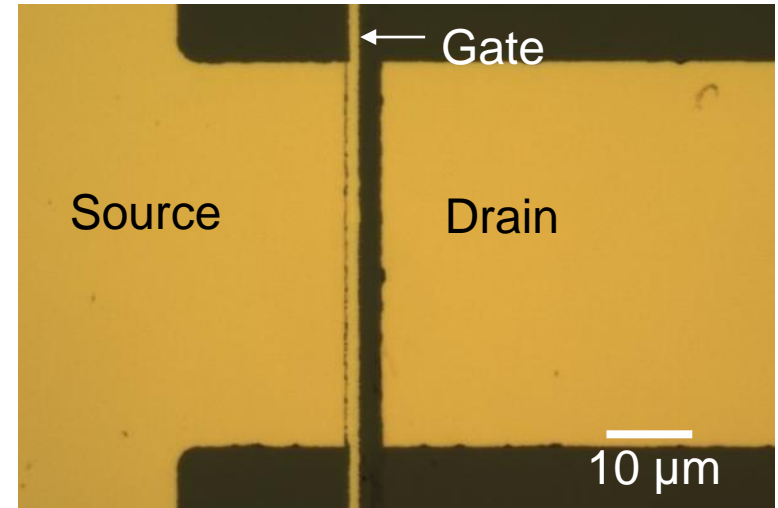
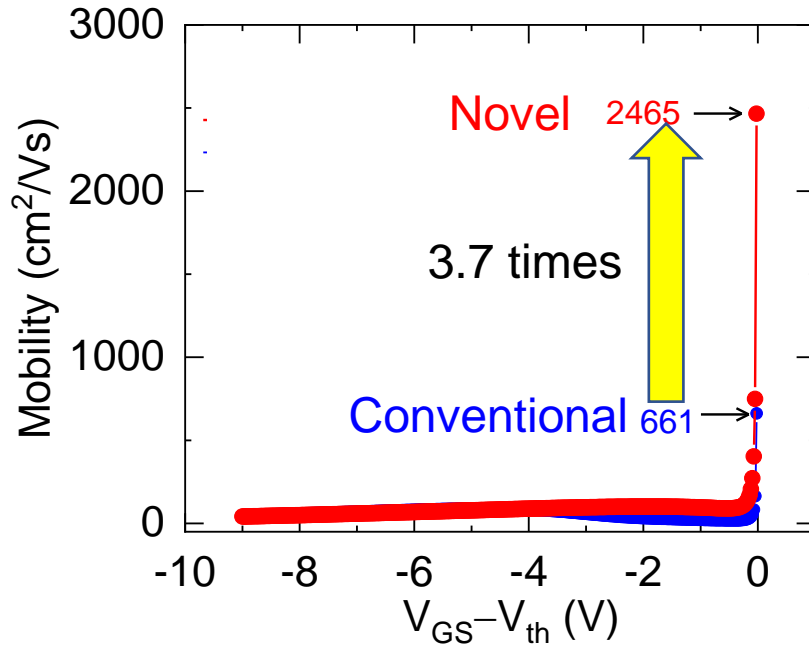
Conventional structure



- Doping layer and carrier transport layer are in close proximity
- Carriers (h) are influenced by acceptor impurities (A⁻), and mobility decreases drastically
- Oxygen in doping layer and hydrogen in carrier transport layer react chemically and the device degrades rapidly

Fig. 5. Extremely high carrier mobility in device characteristics

High carrier mobility ($2465 \text{ cm}^2/\text{Vs}$) close to the realistic value was achieved



Diamond semiconductor device

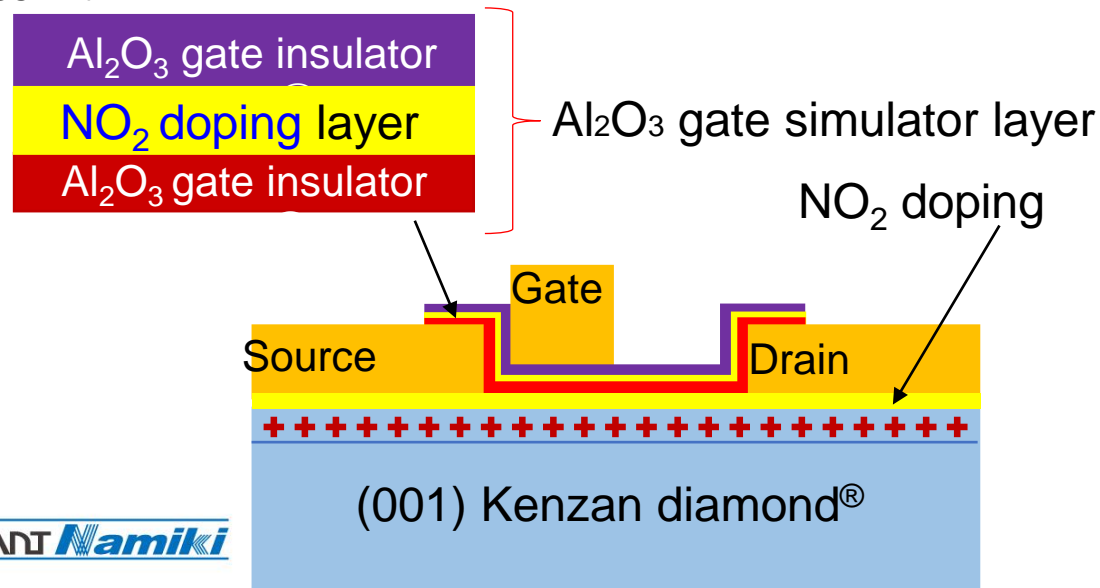
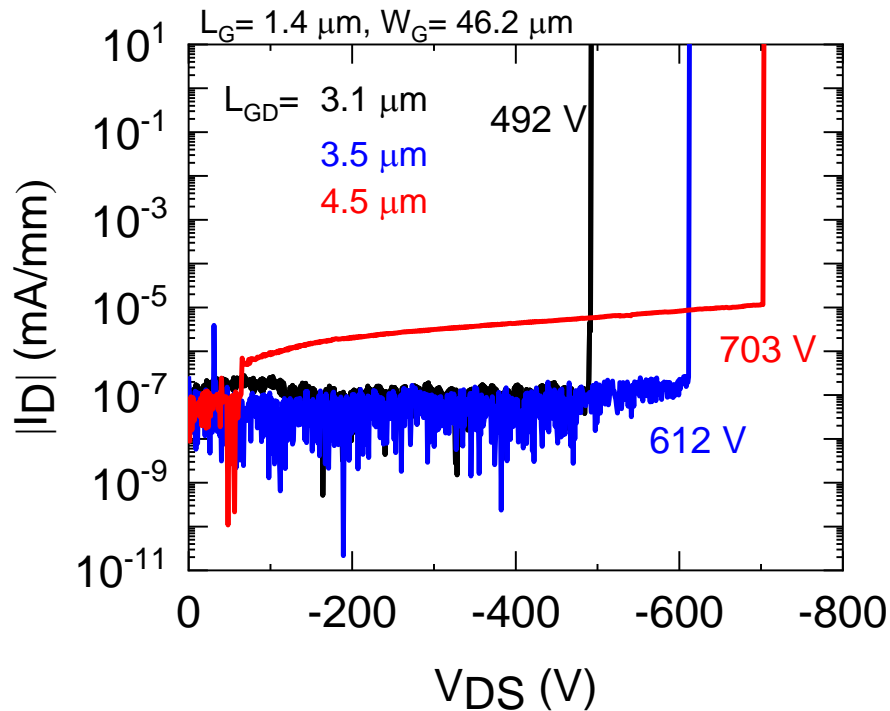


Fig. 6. Technology (3) Highest output power in diamond semiconductor devices

Diamond's highest ever output power of 179 MW/cm²

High voltage



High current

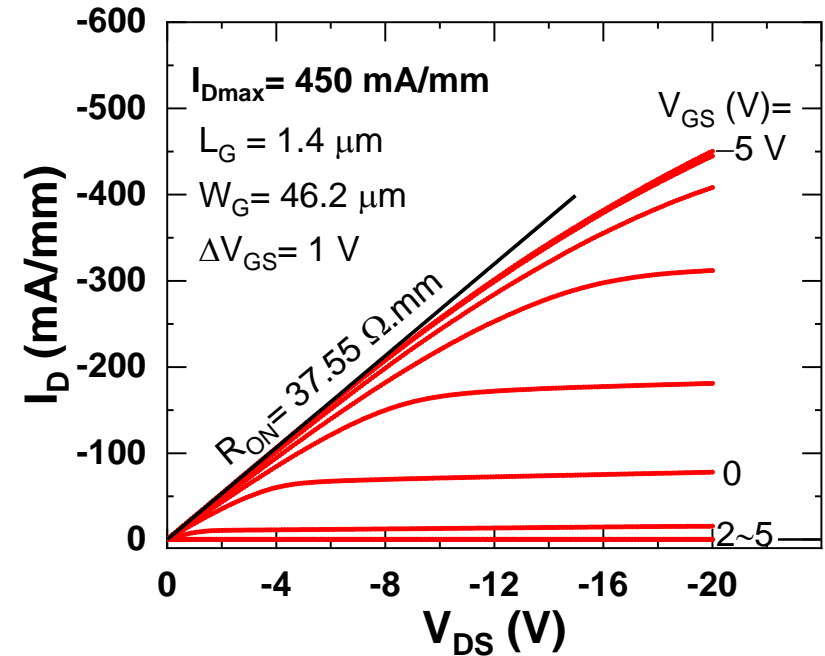
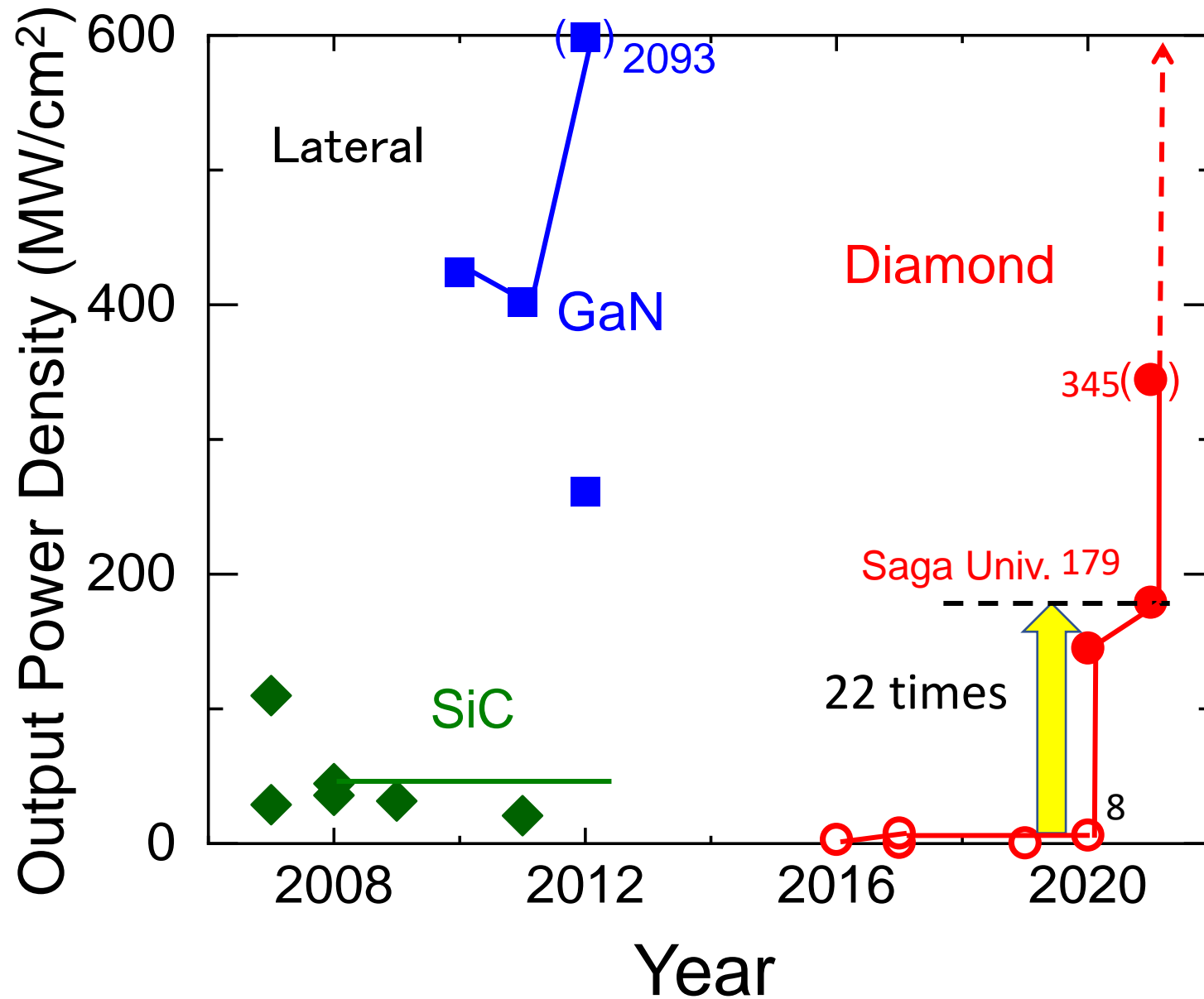


Fig. 7. Roadmap to Beyond-5G communications

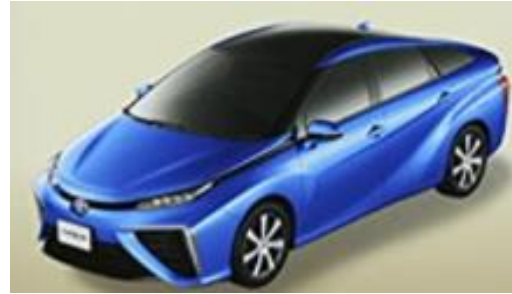


Summary

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- 3) Realization of diamond semiconductor devices with a novel principle.
- 4) Output power density of 179 MW/cm^2 , which is the highest ever reported.
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Appendix. Other possible applications of diamond

【 Power control for electric vehicles 】



- Control smoothly
 - High heat dissipation, No cooling system
- (Source : Kenichi Kawabe, Mechanism of Fuel cell vehicles)

【 Power control for transmission】



- High energy efficiency
 - High voltage, high current
- (Source: Koichi Iwamoto, Offshore wind power generation)

【 Quantum computing 】



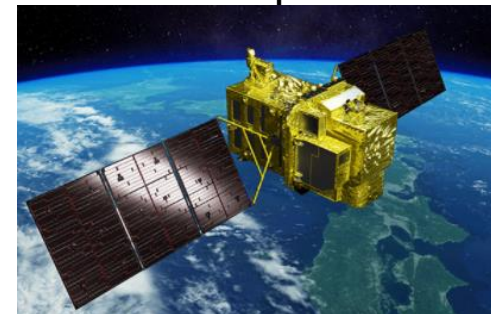
- High speed calculation
 - High energy efficiency
- (Source : Google quantum computer, D-Wave)

【6G】



- High speed communications, high frequency, high power
 - High energy efficiency
- (Source : Tec&Science)

【Aerospace】



- High frequency, high energy efficiency
- High reliability (Source : JAXA Daichi 3, HP)